

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Patent Application of	) Attorney Docket No.: <b>ASAIN0189</b>
	)
Tomoyuki WATANABE et al.	) Confirmation No.: 2626
	)
Serial No.: 10/598,961	) Group Art Unit: 2812
	)
Filed: September 15, 2006	) Examiner: Savitri Mulpuri
	)
For: METHOD FOR MANUFACTURING	) Date: April 23, 2009
SEMICONDUCTOR DEVICE	)

**INFORMATION DISCLOSURE STATEMENT**

**MAIL STOP: Amendment**

United States Patent and Trademark Office  
Customer Service Window  
Randolph Building  
401 Dulany Street  
Alexandria, VA 22314

Sir:

In accordance with the duty of disclosure as set forth in 37 C.F.R. §1.56, this Information Disclosure Statement in connection with the above-identified application is being filed in accordance with 37 C.F.R. §1.97(c).

The documents identified on Form PTO/SB/08A were cited in an Office Action in a corresponding Korean application. Foreign Patent Documents 1 – 3 disclose a method for producing a semiconductor device. In Document 1, in the method, a polysilicon layer 16 and a fluid insulating film 17 are formed on a trench formed by gate electrodes, and a heat treatment is carried out to swell the polysilicon layer 16 so as to densify the fluid insulating film 17. The polysilicon layer 16 may be doped with phosphorus or boron.

In Document 2, in the method, a silicon nitride layer 62 and a polysilicon layer 68 are formed on a trench, and a heat treatment is carried out to swell the polysilicon layer 68 so as

to fill the trench.

In Document 3, in the method, a polysilicon layer 38 doped with phosphorus or arsenic is formed on a trench, and a heat treatment is carried out to swell the polysilicon layer 38. A plurality of the processes for forming the polysilicon layer and plurality of the heat treatments are carried out repeatedly so as to fill the trench.

Accordingly, no further comment with regard to the disclosure of these documents is believed to be required. A copy of each non-U.S. document identified on the attached Form PTO/SB/08A is attached, however, in accordance with Official Gazette Notice dated August 5, 2003, copies of the U.S. patents and patent application publications are not attached.

The Office Action was completed on January 23, 2009, less than three months prior to the filing of this Information Disclosure Statement. Each item of information contained in the Information Disclosure Statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the Information Disclosure Statement.

It is respectfully requested that the attached documents be considered and officially cited, and that the Examiner initial a copy of Form PTO/SB/08A, and return it to the undersigned to indicate that the documents have been considered.

It is believed that the present Information Disclosure Statement complies with the requirements of 37 C.F.R. § 1.97-8, but if the filing of this paper requires fees, the Director is hereby authorized to charge the necessary fees to Deposit Account No. 50-1281.

Respectfully submitted,

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